CoolMOS™ Power Transistor

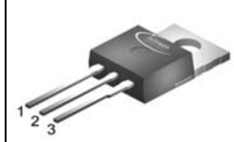
Features

- Lowest figure-of-merit R_{ON} x Q_g
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC[1)] for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge

Product Summary

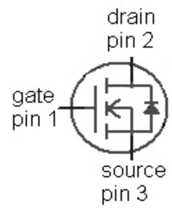
V_{DS} @ T_J=25°C	900	V
$R_{DS(on),max}$ @ T_J= 25°C	0.5	Ω
$Q_{g,typ}$	68	nC

PG-TO220



CoolMOS™ 900V is designed for:

- Quasi Resonant Flyback / Forward topologies
- PC Silverbox and consumer applications
- Industrial SMPS



Type	Package	Marking
IPP90R500C3	PG-TO220	9R500C

Maximum ratings, at T_J=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C	11	A
		T_C=100 °C	6.8	
Pulsed drain current[2)]	$I_{D,pulse}$	T_C=25 °C	24	
Avalanche energy, single pulse	E_{AS}	I_D=2.2 A, V_{DD}=50 V	388	mJ
Avalanche energy, repetitive t_{AR}[2),3)]	E_{AR}	I_D=2.2 A, V_{DD}=50 V	0.74	
Avalanche current, repetitive t_{AR}[2),3)]	I_{AR}		2.2	A
MOSFET dv/dt ruggedness	dv/dt	V_{DS}=0...400 V	50	V/ns
Gate source voltage	V_{GS}	static	±20	V
		AC (f>1 Hz)	±30	
Power dissipation	P_{tot}	T_C=25 °C	156	W
Operating and storage temperature	T_J, T_{stg}		-55 ... 150	°C
Mounting torque		M3 and M3.5 screws	60	Ncm

Maximum ratings, at T_J=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	T_C=25 °C	6.6	A
Diode pulse current[2]	$I_{S,pulse}$		23	
Reverse diode dv/dt[4]	dv/dt		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	0.8	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C
Electrical characteristics, at T_J=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	900	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.74 mA	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=900 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=900 V, V_{GS}=0 V, T_j=150 °C	-	10	-	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=6.6 A, T_j=25 °C	-	0.39	0.5	Ω
		V_{GS}=10 V, I_D=6.6 A, T_j=150 °C	-	1.1	-	
Gate resistance	R_G	f=1 MHz, open drain	-	1.3	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz	-	1700	-	pF
Output capacitance	C_{oss}		-	83	-	
Effective output capacitance, energy related [5]	$C_{o(er)}$	V_{GS}=0 V, V_{DS}=0 V to 500 V	-	52	-	
Effective output capacitance, time related [6]	$C_{o(tr)}$		-	200	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400 V, V_{GS}=10 V, I_D=6.6 A, R_G=30.9 Ω	-	70	-	ns
Rise time	t_r		-	20	-	
Turn-off delay time	$t_{d(off)}$		-	400	-	
Fall time	t_f		-	25	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=400 V, I_D=6.6 A, V_{GS}=0 to 10 V	-	8	-	nC
Gate to drain charge	Q_{gd}		-	29	-	
Gate charge total	Q_g		-	68	tbd	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=6.6 A, T_j=25 °C	-	0.8	1.2	V
Reverse recovery time	t_{rr}	V_R=400 V, I_F=I_S, di_F/dt=100 A/µs	-	480	-	ns
Reverse recovery charge	Q_{rr}		-	8.5	-	µC
Peak reverse recovery current	I_{rrm}		-	31	-	A

[1] J-STD20 and JESD22

[2] Pulse width t_p limited by $T_{J,max}$

[3] Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

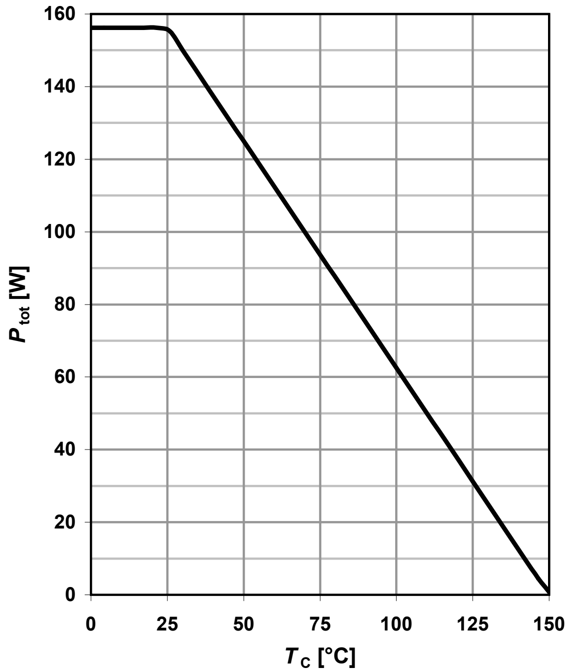
[4] $I_{SD} \leq I_D$, di/dt≤ 200 A/µs, V_{DClink}=400V, $V_{peak}<V_{(BR)DSS}$, $T_J<T_{J,max}$, identical low side and high side switch

[5] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 50% $V_{DSS.}$

[6] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 50% $V_{DSS.}$

1 Power dissipation

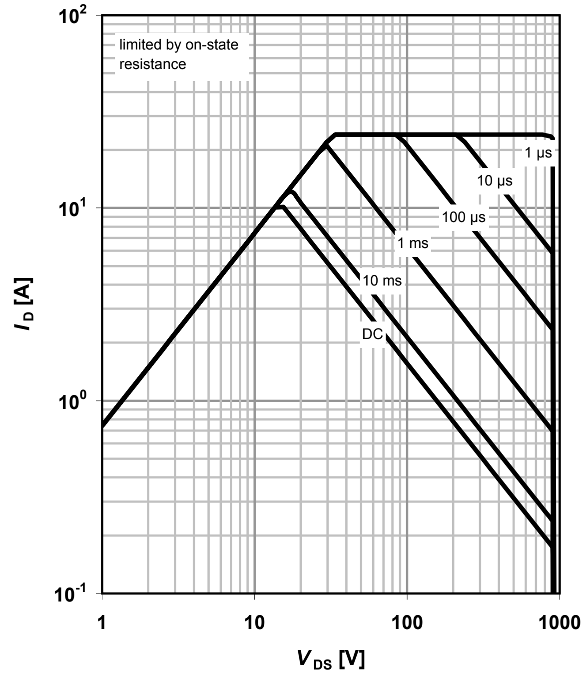
P_{tot}=f(T_C)



2 Safe operating area

I_D=f(V_{DS}); T_C=25 °C; D=0

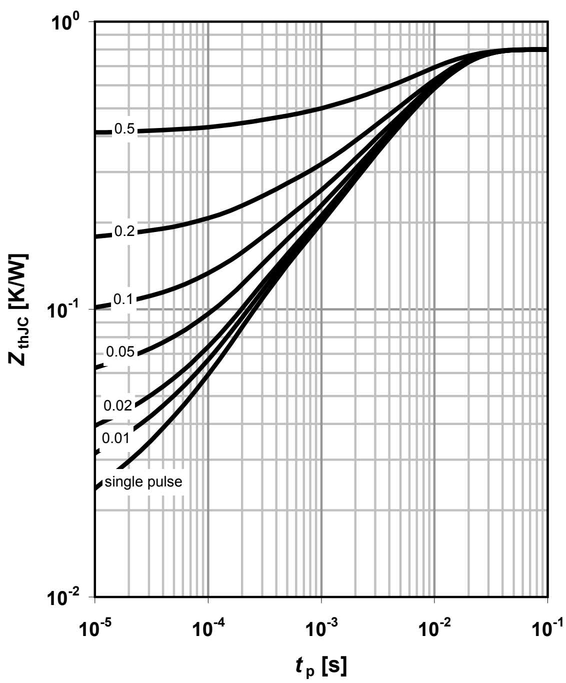
parameter: t_p



3 Max. transient thermal impedance

Z_{thJC}=f(t_P)

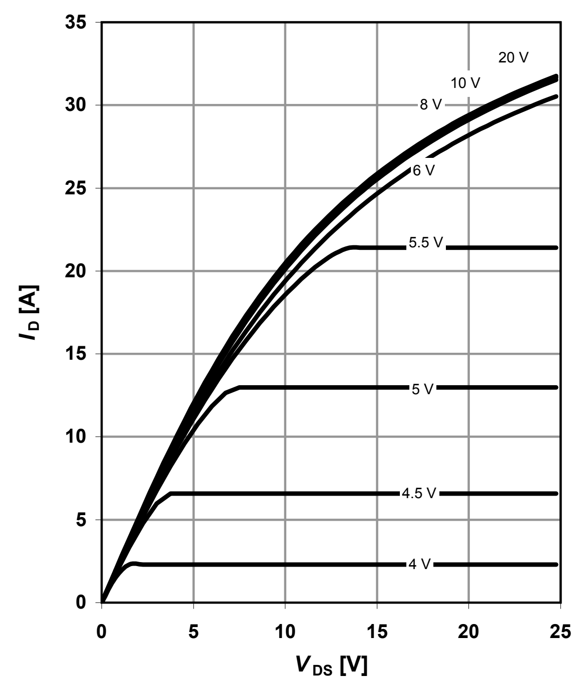
parameter: D=t_p/T



4 Typ. output characteristics

I_D=f(V_{DS}); T_J=25 °C

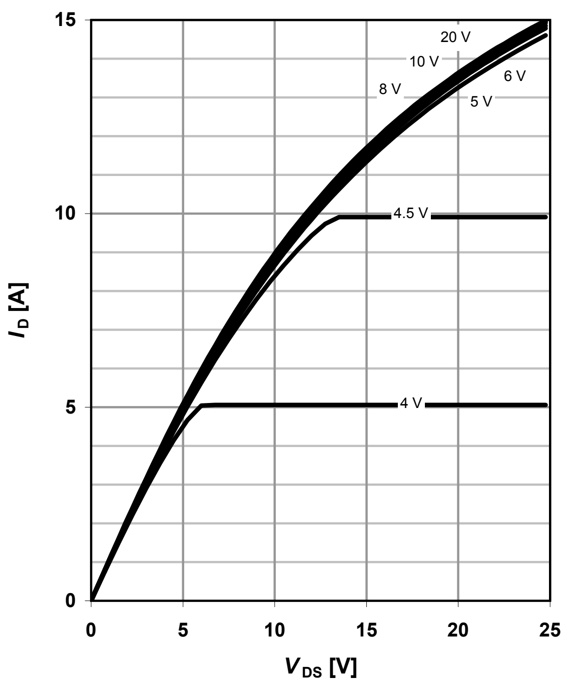
parameter: V_{GS}



5 Typ. output characteristics

I_D=f(V_{DS}); T_J=150 °C

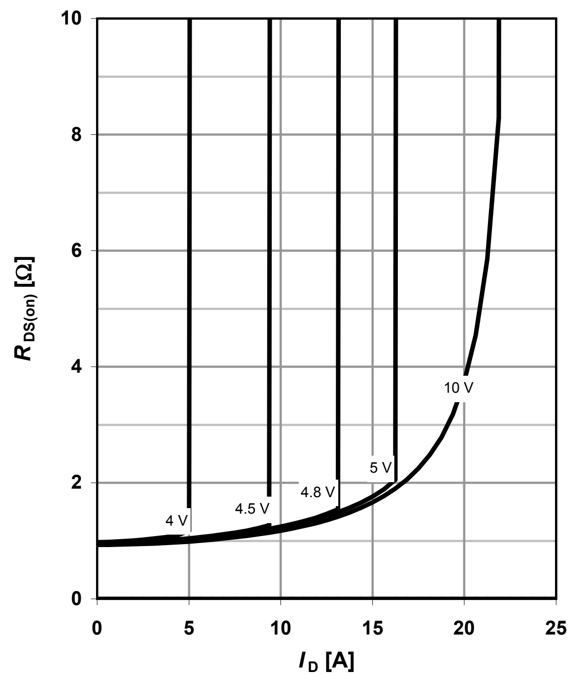
parameter: V_{GS}



6 Typ. drain-source on-state resistance

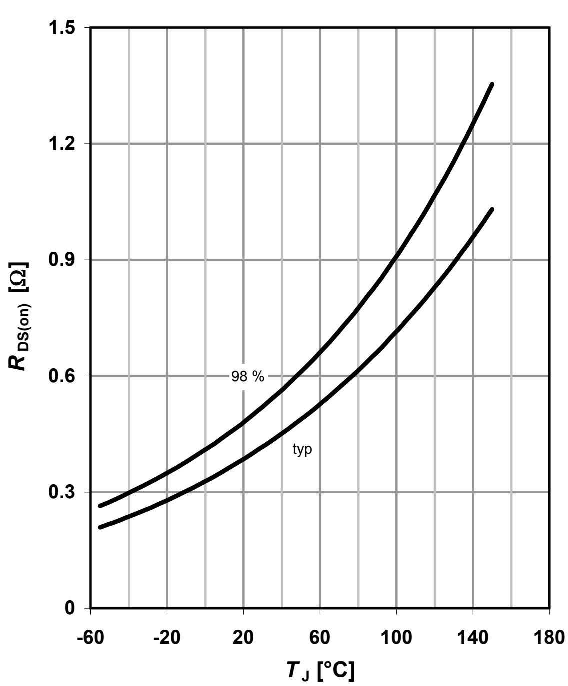
$R_{DS(on)}$=f(I_D); T_J=150 °C

parameter: V_{GS}



7 Drain-source on-state resistance

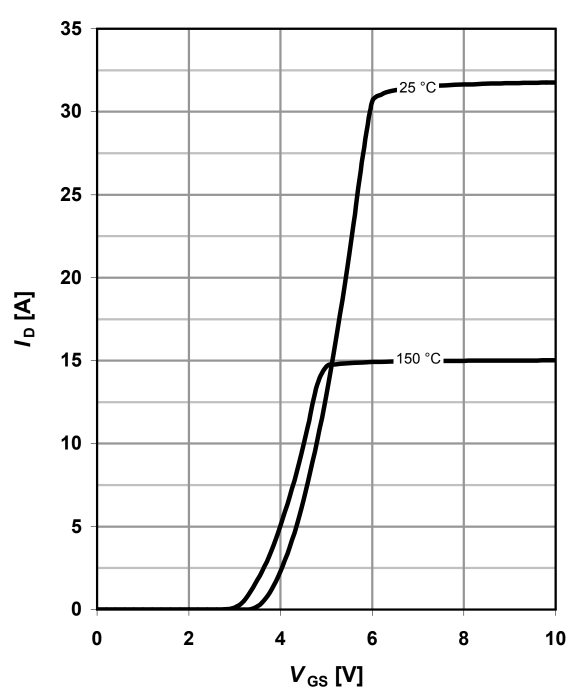
$R_{DS(on)}$=f(T_J); I_D=6.6 A; V_{GS}=10 V



8 Typ. transfer characteristics

I_D=f(V_{GS}); V_{DS}=20V

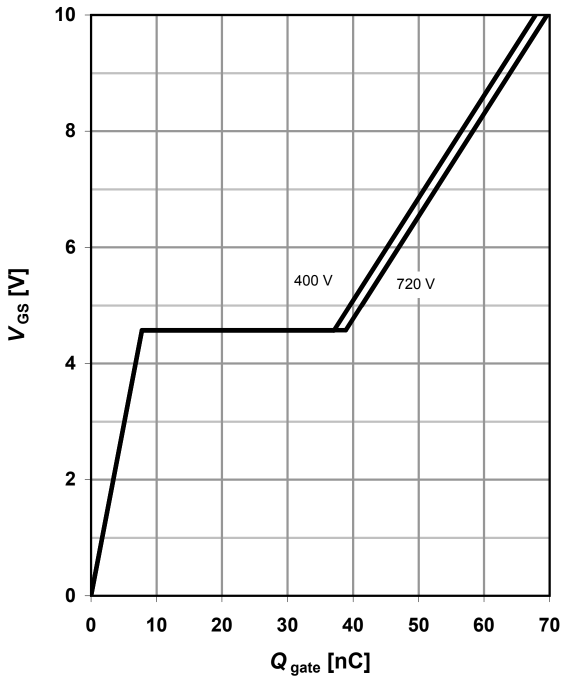
parameter: T_J



9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=6.6 A pulsed

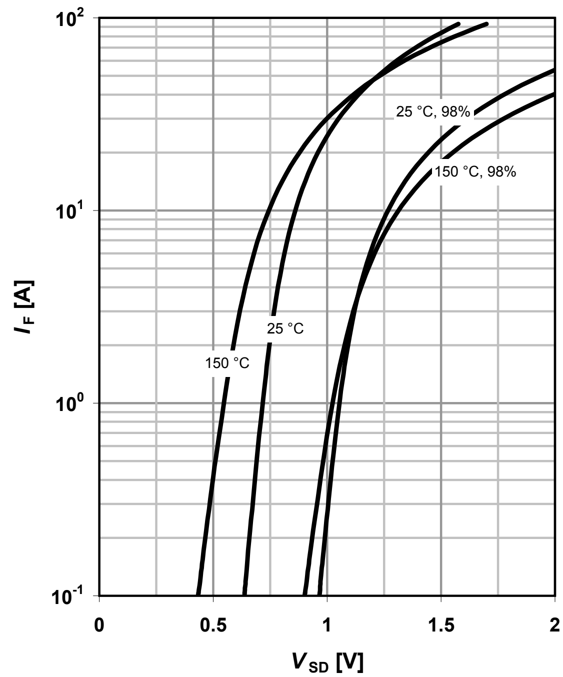
parameter: V_{DD}



10 Forward characteristics of reverse diode

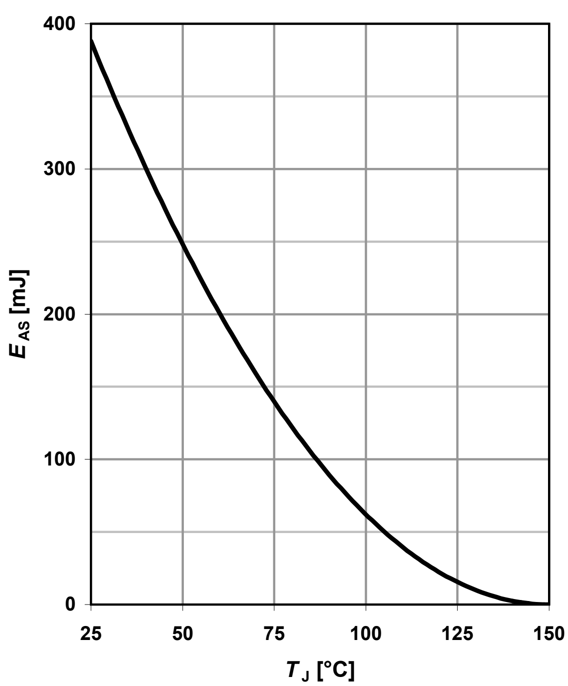
I_F=f(V_{SD})

parameter: T_J



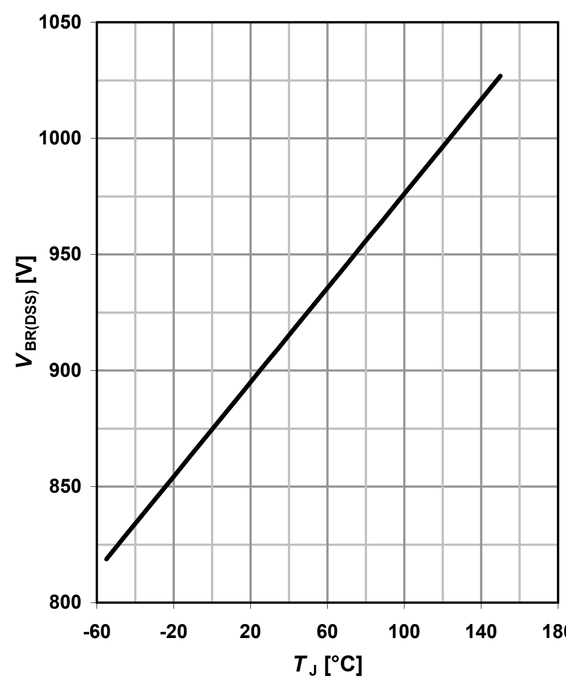
11 Avalanche energy

E_{AS}=f(T_J); I_D=2.2 A; V_{DD}=50 V



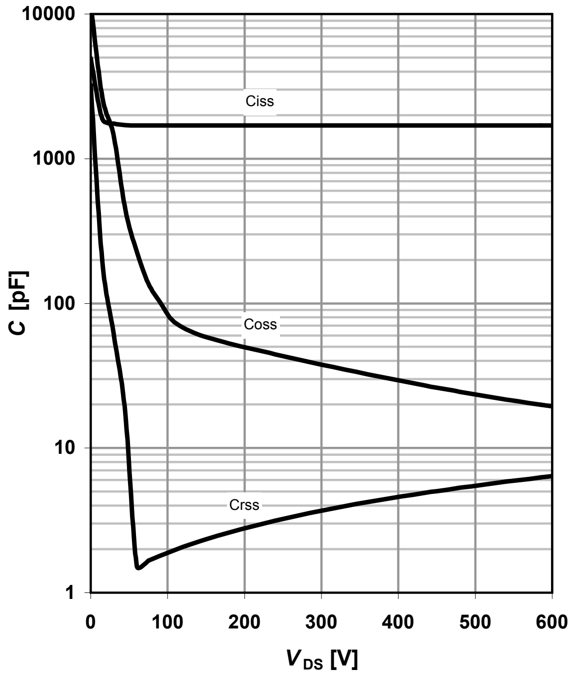
12 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_J); I_D=0.25 mA



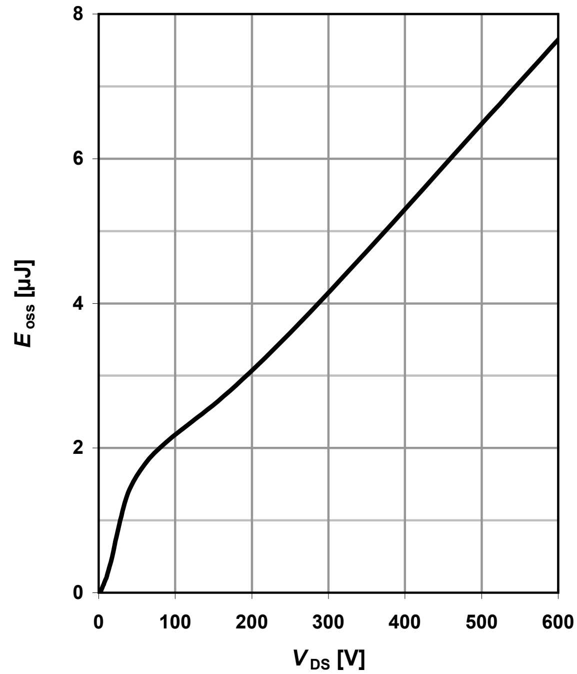
13 Typ. capacitances

$C = f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

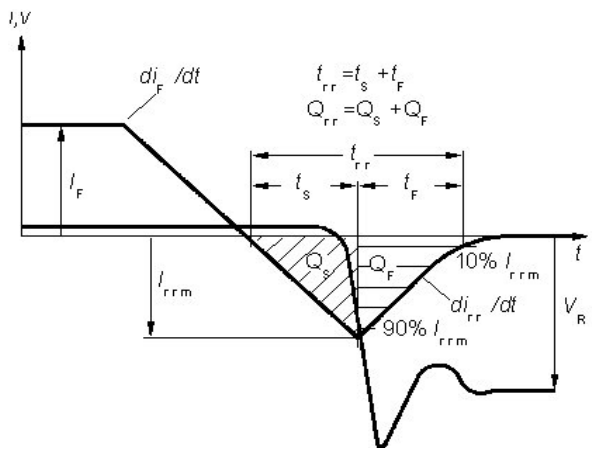


14 Typ. C_{oss} stored energy

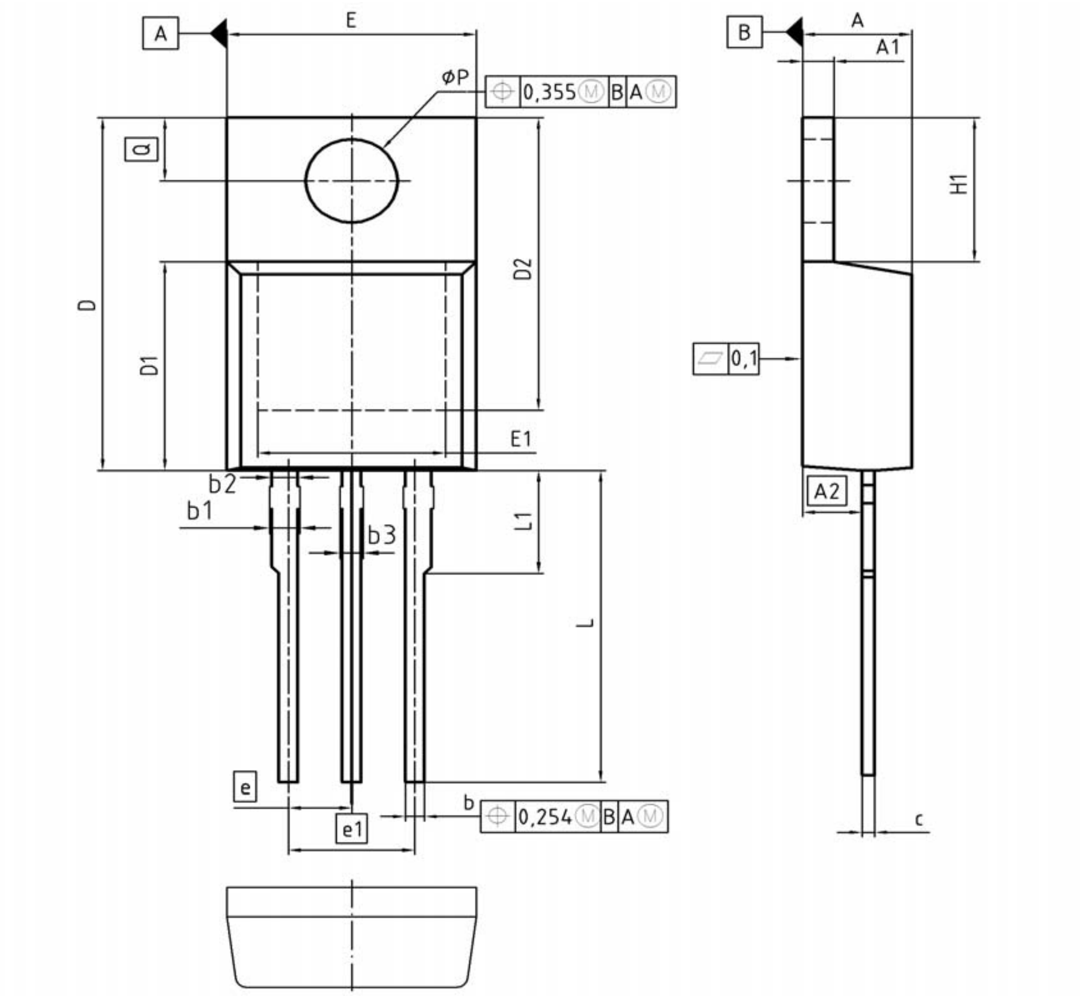
$E_{oss} = f(V_{DS})$



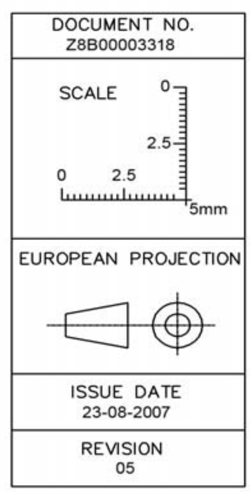
Definition of diode switching characteristics



PG-TO220 Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118



Dimensions in mm/inches

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